

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1746779	mos device	USPAT	OR	OFF	2005/01/13 10:57
L2	1764494	rom device	USPAT	OR	OFF	2005/01/13 11:08
L3	23893	2 and trench	USPAT	OR	OFF	2005/01/13 10:53
L4	11994	3 and thermal	USPAT	OR	OFF	2005/01/13 10:53
L5	10737	4 and oxide	USPAT	OR	OFF	2005/01/13 10:53
L6	997	5 and (second adj polysilicon)	USPAT	OR	OFF	2005/01/13 10:54
L7	0	6 and chanel	USPAT	OR	OFF	2005/01/13 10:54
L8	679	6 and channel	USPAT	OR	OFF	2005/01/13 11:08
L9	543	8 and implantation	USPAT	OR	OFF	2005/01/13 11:10
L10	27	9 and (mos adj device)	USPAT	OR	OFF	2005/01/13 10:58
L11	10	9 and (rom adj device)	USPAT	OR	OFF	2005/01/13 10:58
L12	2175	rom adj device	USPAT	OR	OFF	2005/01/13 11:08
L13	343897	2 and channel	USPAT	OR	OFF	2005/01/13 11:09
L14	945	12 and channel	USPAT	OR	OFF	2005/01/13 11:09
L15	249	14 and implantation	USPAT	OR	OFF	2005/01/13 11:10